

TOSHIBA GTR MODULE SILICON N-CHANNEL IGBT

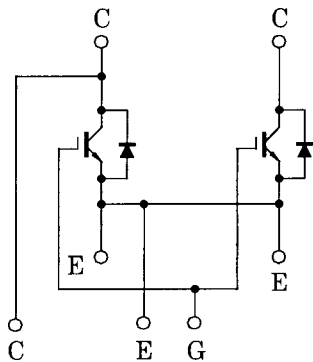
# MG1200V1US51

HIGH POWER SWITCHING APPLICATIONS  
MOTOR CONTROL APPLICATIONS

## FEATURES

- High Input Impedance
- Enhancement Mode
- Electrodes are isolated from case.

## EQUIVALENT CIRCUIT



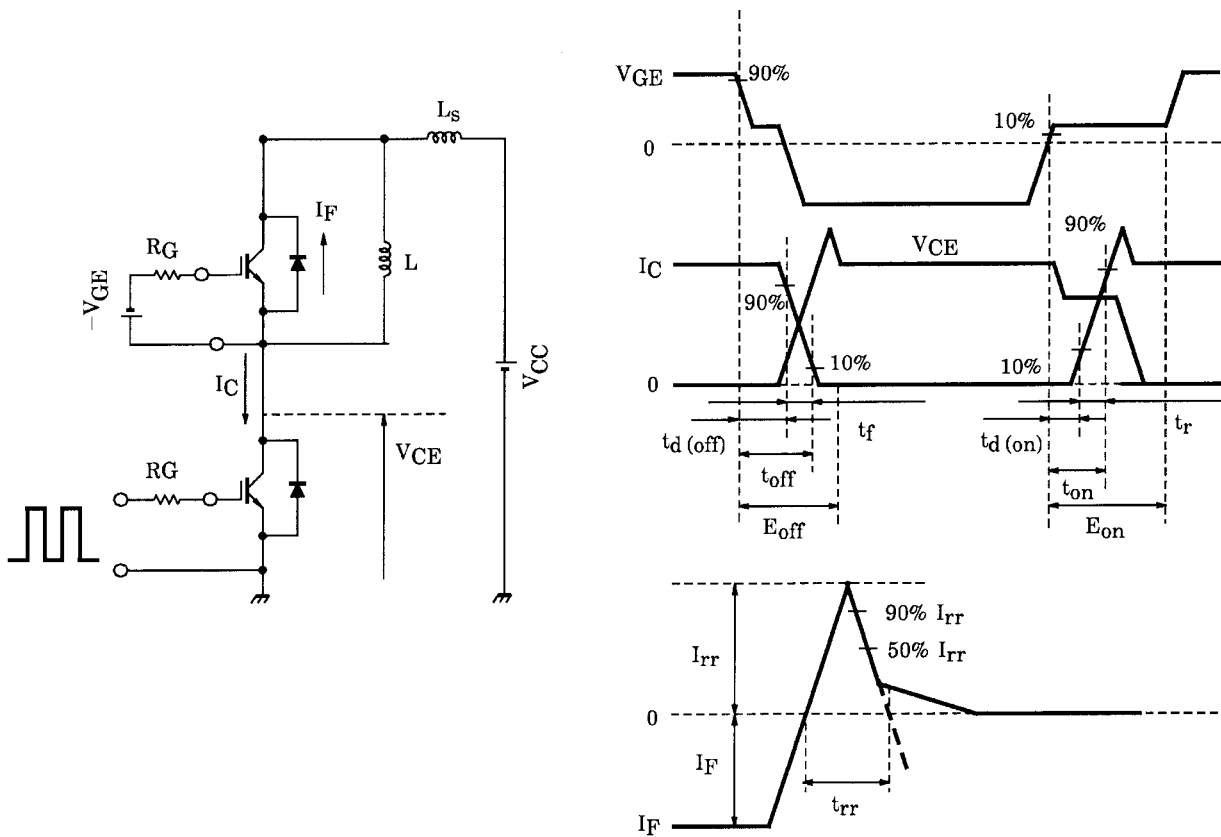
## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTICS		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	1700	V
Gate-Emitter Voltage		V <sub>GES</sub>	20	V
Collector Current	DC	I <sub>C</sub>	1200	A
	1ms	I <sub>CP</sub>	2400	
Forward Current	DC	I <sub>F</sub>	1200	A
	1ms	I <sub>FM</sub>	2400	
Collector Power Dissipation (T <sub>c</sub> = 25°C)		P <sub>C</sub>	5560	W
Junction Temperature		T <sub>j</sub>	-20~125	°C
Storage Temperature Range		T <sub>stg</sub>	-40~125	°C
Isolation Voltage		V <sub>Isol</sub>	5400 (AC 1min)	V
Screw Torque	Terminal: M4/M8	—	2 / 7	N·m
	Mounting		4	

**ELECTRICAL CHARACTERISTICS (Tc = 125°C : except thermal resistance)**

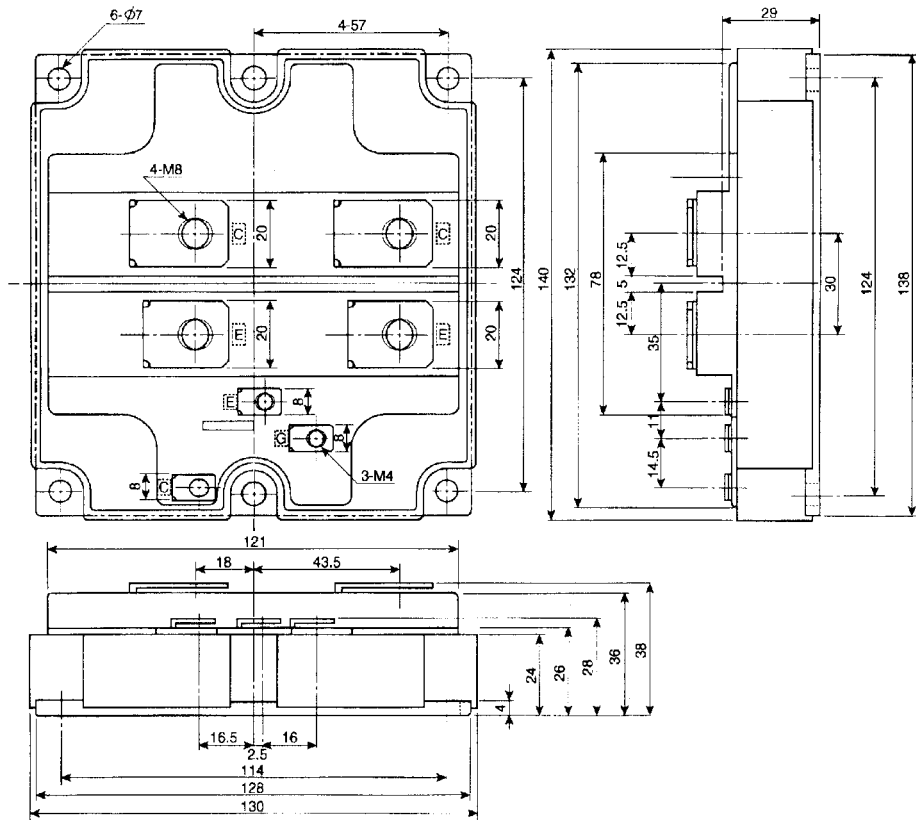
CHARACTERISTICS		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		$I_{GES}$	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	—	—	$\pm 50$	nA
Collector Cut-Off Current		$I_{CES}$	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}$	—	—	100	mA
Gate-Emitter Cut-Off Voltage		$V_{GE(off)}$	$V_{CE} = 5\text{ V}, I_C = 1.2\text{ A}$	3.0	—	7.0	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 1200\text{ A}$	—	—	5.0	V
Input Capacitance		$C_{ies}$	$V_{CE} = 10\text{ V}, V_{GE} = 0\text{ V}, f = 300\text{ kHz}$	—	130	—	nF
Switching Time (Note 1)	Rise Time	$t_r$	$V_{CC} = 900\text{ V}, I_C = 1200\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 1.8\ \Omega$ (Inductive load: $L_s = 150\text{ nH}$ )	—	—	0.7	$\mu\text{s}$
	Turn-On Time	$t_{on}$		—	—	1.0	$\mu\text{s}$
	Fall Time	$t_f$		—	—	0.8	$\mu\text{s}$
	Turn-Off Time	$t_{off}$		—	—	1.5	$\mu\text{s}$
Forward Voltage		$V_F$	$I_F = 1200\text{ A}, V_{GE} = 0\text{ V}$	—	—	3.2	V
Reverse Recovery Time (Note 1)		$t_{rr}$	$I_F = 1200\text{ A}, V_{GE} = 15\text{ V}$ $di/dt = 4000\text{ A}/\mu\text{s}, V_{CC} = 900\text{ V}$	—	—	0.8	$\mu\text{s}$
Switching Dissipation (Note 1)	Turn-On Loss	$E_{on}$	$V_{CC} = 900\text{ V}, I_C = 1200\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 1.8\ \Omega$	—	250	—	mJ
	Turn-Off Loss	$E_{off}$		—	500	—	mJ
	Diode Loss	$E_{dsw}$	$I_F = 1200\text{ A}, V_{GE} = -15\text{ V}$ $di/dt = 4000\text{ A}/\mu\text{s}, V_{CC} = 900\text{ V}$	—	300	—	mJ
Thermal Resistance		$R_{th(j-c)}$	Transistor (IGBT) Stage	—	—	0.018	$^{\circ}\text{C}/\text{W}$
			Diode Stage	—	—	0.035	$^{\circ}\text{C}/\text{W}$

Note 1: Test circuit and timing chart of switching time, reverse recovery time and switching dissipation.



## PACKAGE DIMENSIONS: TOSHIBA 2-142A1A

Unit: mm



Weight: 900 g (typ.)

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